MICROWAVE POWER GaAs FET TIM6472-16UL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- BROAD BAND INTERNALLY MATCHED FET
- HIGH POWER
 - P1dB= 42.5dBm at 6.4GHz to 7.2GHz

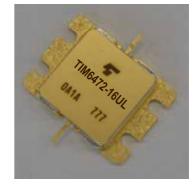
·HIGH GAIN

G1dB= 9.5dB at 6.4GHz to 7.2GHz

·LOW INTERMODULATION DISTORTION

IM3 = -44dBc(Min.) at Pout= 31.5dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 3.6A f= 6.4 to 7.2GHz	dBm	41.5	42.5	
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.5	9.5	
Drain Current	IDS1		А		4.4	5.0
Gain Flatness	ΔG		dB			±0.6
Power Added Efficiency	ηadd		%		36	
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 31.5dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-44	-47	
Drain Current	IDS2		А		4.4	5.0
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin –P1dB) × Rth(c-c)	°C			80

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 68 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

				1	1	
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 6.0A	S	_	3.6	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 60mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	10.5	_
Gate-Source Breakdown Voltage	VGSO	IGS= -200µA	V	-5	_	
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.5	1.8

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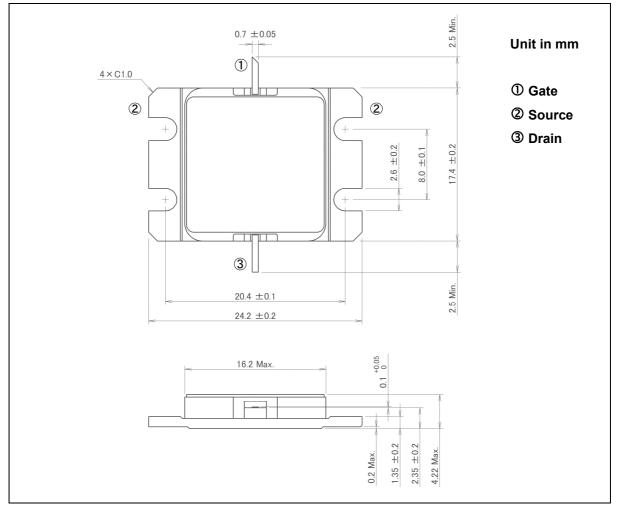
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	14.0
Total Power Dissipation (Tc= 25°C)	PT	W	83.3
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-16G1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

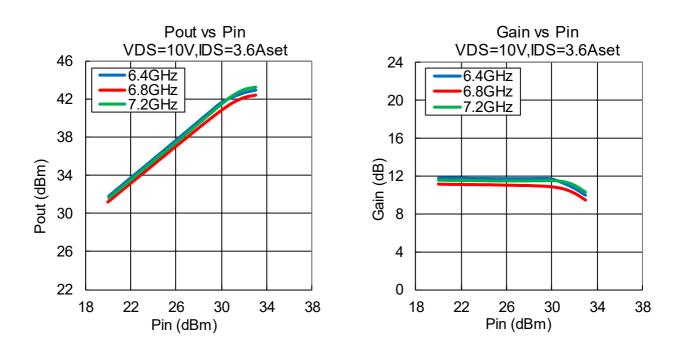
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

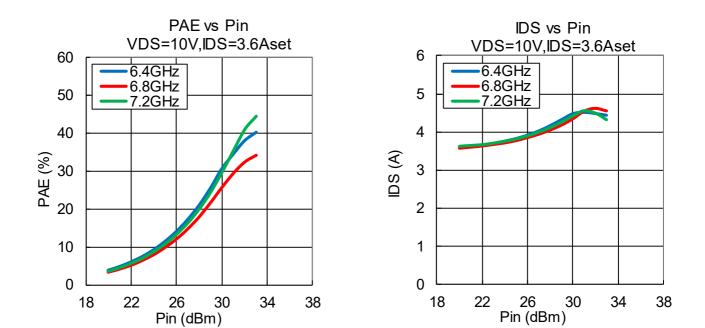
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 3.6 A, f= 6.4, 6.8, 7.2 GHz, Ta= +25 °C



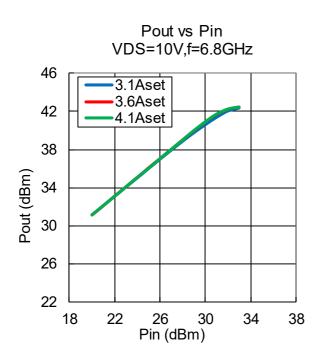


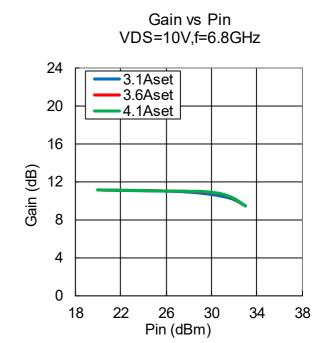
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

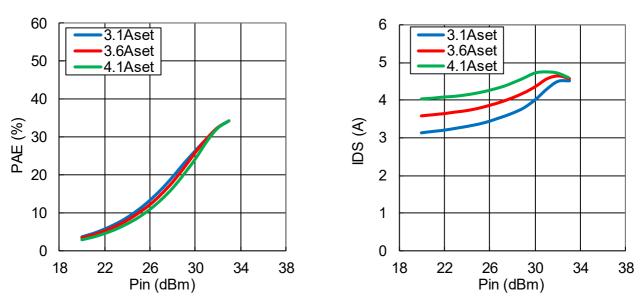
VDS= 10 V, IDSset= 3.1, 3.6, 4.1 A, f= 6.8 GHz, Ta= +25 °C





PAE vs Pin VDS=10V,f=6.8GHz

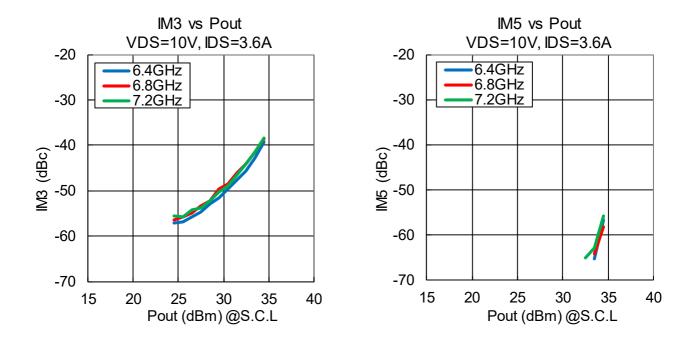
IDS vs Pin VDS=10V,f=6.8GHz



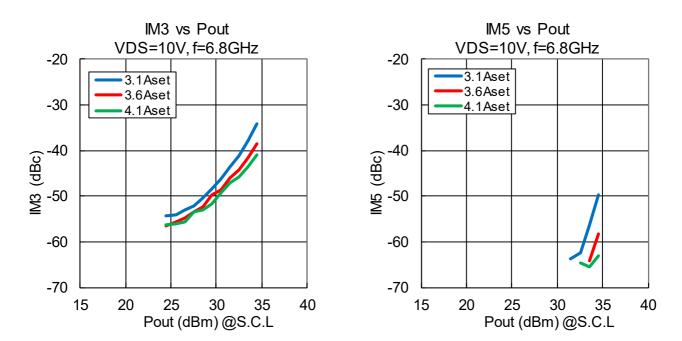
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·IM3, IM5 vs. Pout

VDS= 10 V, IDSset= 3.6 A, f= 6.4, 6.8, 7.2 GHz, Δf= 5 MHz , Ta= +25 °C



VDS= 10 V, IDSset= 3.1, 3.6, 4.1 A, f= 6.8 GHz, Δf= 5 MHz , Ta= +25 °C

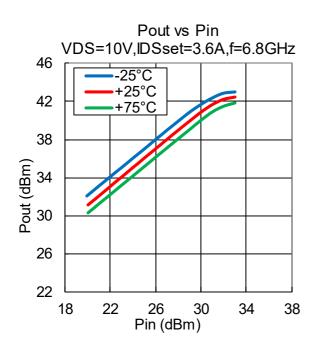


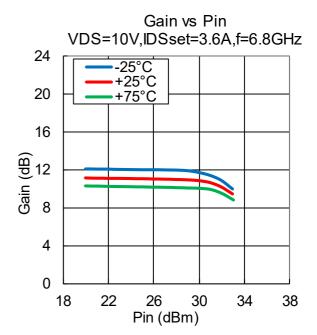
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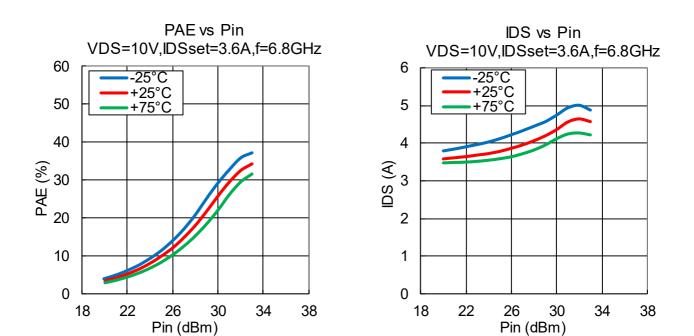
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout , Gain , PAE , IDS vs. Pin vs. Temperature

VDS= 10 V, IDSset= 3.6 A, f= 6.8 GHz, Ta= -25, +25, +75 °C



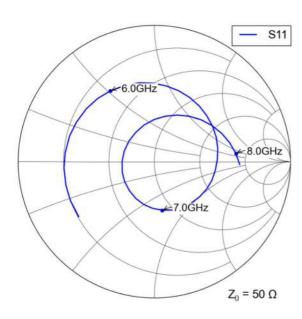


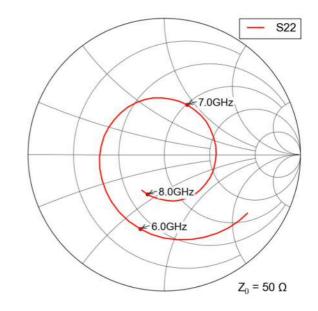


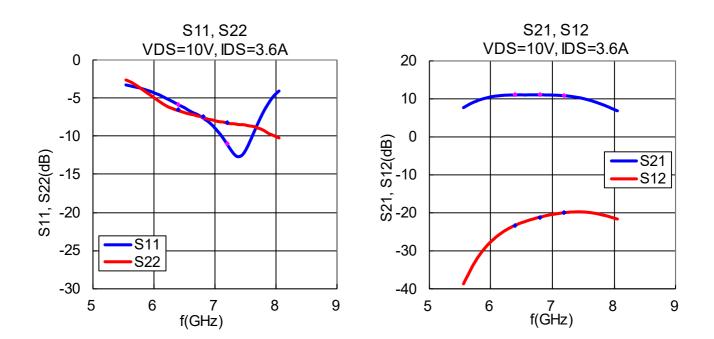
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·S-Parameters

VDS= 10 V, IDSset= 3.6 A, f= 5.55 to 8.05 GHz, Ta= +25 ℃







MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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